

# Nch 600V 95mohm(typ.) Power MOSFET

| V <sub>DSS</sub> (@Tj max.)*5 | 650V   |
|-------------------------------|--------|
| R <sub>DS(on)</sub> (Max.)    | 0.114Ω |
| I <sub>DP</sub> *2            | ±105A  |
| P <sub>D</sub>                | 347W   |

# Outline TO-220AB

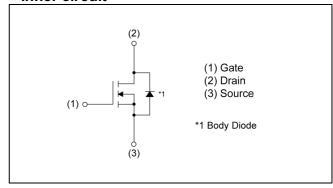
# Features

- 1) Fast reverse recovery time (trr)
- 2) Low on-resistance
- 3) Fast switching speed
- 4) Drive circuits can be simple
- 5) Pb-free plating; RoHS compliant
- 6) Halogen free mold compound

# Application

Switching applications

# •Inner circuit



| Marking | R6035VNX3 |
|---------|-----------|

# ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

| Parameter  | Symbol             | Value       | Unit |
|--|--------------------|-------------|------|
| Drain - Source voltage                           | V <sub>DSS</sub>   | 600         | V    |
| Continuous drain current (T <sub>c</sub> = 25°C) | I <sub>D</sub> *1  | ±35         | Α    |
| Pulsed drain current                             | I <sub>DP</sub> *2 | ±105        | Α    |
| Gate - Source voltage                            | V <sub>GSS</sub>   | ±30         | V    |
| Avalanche current, single pulse                  | I <sub>AS</sub> *3 | 2.3         | Α    |
| Avalanche energy, single pulse                   | E <sub>AS</sub> *3 | 148         | mJ   |
| MOSFET dv/dt                                     | dv/dt*4            | 120         | V/ns |
| Power dissipation (T <sub>c</sub> = 25°C)        | P <sub>D</sub>     | 347         | W    |
| Junction temperature                             | T <sub>j</sub>     | 150         | °C   |
| Operating junction and storage temperature range | T <sub>stg</sub>   | -55 to +150 | °C   |

R6035VNX3

# ●Thermal resistance

| Downwortow                                   | O                 | Values |      |      | 1.1  |
|--|-------------------|--------|------|------|------|
| Parameter                                    | Symbol            | Min.   | Тур. | Max. | Unit |
| Thermal resistance, junction - case          | R <sub>thJC</sub> | -      | -    | 0.36 | °C/W |
| Thermal resistance, junction - ambient       | R <sub>thJA</sub> | -      | -    | 62.5 | °C/W |
| Soldering temperature, wavesoldering for 10s | T <sub>sold</sub> | -      | -    | 265  | °C   |

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

| Darameter                           | Cumb al                | Conditions                                   | Values |       |       | Unit  |
|-------------------------------------|------------------------|--|--------|-------|-------|-------|
| Parameter                           | Symbol                 | Conditions                                   | Min.   | Тур.  | Max.  | Offic |
| Drain - Source breakdown<br>voltage | V <sub>(BR)DSS</sub>   | $V_{GS} = 0V$ , $I_D = 1mA$                  | 600    | -     | 1     | V     |
| Zero gate voltage<br>drain current  | I <sub>DSS</sub>       | V <sub>DS</sub> = 600V, V <sub>GS</sub> = 0V | -      | -     | 100   | μA    |
| Gate - Source leakage current       | I <sub>GSS</sub>       | $V_{GS} = \pm 30V$ , $V_{DS} = 0V$           | -      | -     | ±100  | nA    |
| Gate threshold voltage              | V <sub>GS(th)</sub>    | $V_{DS} = V_{GS}, I_{D} = 1.1 \text{mA}$     | 4.5    | 5.5   | 6.5   | V     |
| Static drain - source               | D *5                   | V <sub>GS</sub> = 15V, I <sub>D</sub> = 8A   | -      | 0.095 | 0.114 | Ω     |
| on - state resistance               | R <sub>DS(on)</sub> *5 | V <sub>GS</sub> = 10V, I <sub>D</sub> = 8A   | -      | 0.099 | 0.119 | Ω     |
| Gate resistance                     | $R_{G}$                | f = 1MHz, open drain                         | -      | 1.7   | -     | Ω     |

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

| Davanastav                                  | Company of               | Conditions                                   | Values |      |      | Linit |
|---|--------------------------|--|--------|------|------|-------|
| Parameter                                   | Symbol                   | Conditions                                   | Min.   | Тур. | Max. | Unit  |
| Input capacitance                           | C <sub>iss</sub>         | V <sub>GS</sub> = 0V, V <sub>DS</sub> = 100V | -      | 2400 | -    |       |
| Output capacitance                          | C <sub>oss</sub>         | f = 100kHz                                   | -      | 80   | -    |       |
| Effective output capacitance energy related | C <sub>o(er)</sub> *6    | V <sub>GS</sub> = 0V                         | -      | 80   | -    | pF    |
| Effective output capacitance time related   | C <sub>o(tr)</sub> *7    | V <sub>DS</sub> = 0V to 480V                 | -      | 490  | 1    |       |
| Turn - on delay time                        | t <sub>d(on)</sub> *5    | $V_{DD} \simeq 300V$ , $V_{GS} = 15V$        | -      | 34   | -    |       |
| Rise time                                   | t <sub>r</sub> *5        | I <sub>D</sub> = 8A                          | -      | 18   | -    |       |
| Turn - off delay time                       | t <sub>d(off)</sub> *5   | R <sub>L</sub> ~ 37.5Ω                       | -      | 81   | -    | ns    |
| Fall time                                   | <b>t</b> <sub>f</sub> *5 | $R_G = 10\Omega$                             | -      | 10   | -    |       |

# • Gate charge characteristics ( $T_a = 25$ °C)

| Darameter            | Cumb al                | Conditions                        | Values |      |      | Lloit |
|----------------------|------------------------|-----------------------------------|--------|------|------|-------|
| Parameter            | Symbol                 | Conditions                        | Min.   | Тур. | Max. | Unit  |
| Total gate charge    | $Q_g^{*5}$             | V <sub>DD</sub> ≈ 300V            | -      | 50   | 1    |       |
| Gate - Source charge | Q <sub>gs</sub> *5     | I <sub>D</sub> = 8A               | -      | 20   | 1    | nC    |
| Gate - Drain charge  | $Q_{gd}^{*5}$          | V <sub>GS</sub> = 10V             | -      | 22   | 1    |       |
| Gate plateau voltage | V <sub>(plateau)</sub> | $V_{DD} \simeq 300V$ , $I_D = 8A$ | _      | 8.3  | -    | V     |

# ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

| Parameter                     | Cumph of           | Conditions   | Values |      |      | Unit |  |
|-------------------------------|--------------------|--|--------|------|------|------|--|
| Parameter                     | Symbol             | Conditions   | Min.   | Тур. | Max. | Uill |  |
| Source current                | I <sub>S</sub> *1  | T = 25°C   | -      | 1    | 35   | Α    |  |
| Pulsed source current         | I <sub>SP</sub> *2 | T <sub>C</sub> = 25°C  | -      | 1    | 105  | Α    |  |
| Source-Drain voltage          | $V_{SD}^{*5}$      | $V_{GS} = 0V, I_{S} = 8A$  | -      | -    | 1.5  | V    |  |
| Reverse recovery time         | t <sub>rr</sub> *5 | V <sub>DD</sub> ≃ 400V<br>I <sub>S</sub> = 8A<br>di/dt = 100A/μs | -      | 92   | -    | ns   |  |
| Reverse recovery charge       | Q <sub>rr</sub> *5 |  | -      | 391  | -    | nC   |  |
| Peak reverse recovery current | <sub>rr</sub> *5   |  | -      | 8.3  | -    | Α    |  |

<sup>\*1</sup> Limited only by maximum channel temperature allowed.

<sup>\*2</sup> Pw  $\leq$  10µs, Duty cycle  $\leq$  1%

<sup>\*3</sup> L $\doteqdot$ 50mH, V<sub>DD</sub>=50V, R<sub>G</sub>=25 $\Omega$ , STARTING T<sub>i</sub>=25 $^{\circ}$ C

<sup>\*4</sup>  $V_{DS}$  = 0 to 400V

<sup>\*5</sup> Pulsed

<sup>\*6</sup> Co(er) is a fixed capacitance that gives the same stored energy as Coss while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>\*7</sup> Co(tr) is a fixed capacitance that gives the same charging time as Coss while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

Fig.1 Power Dissipation Derating Curve

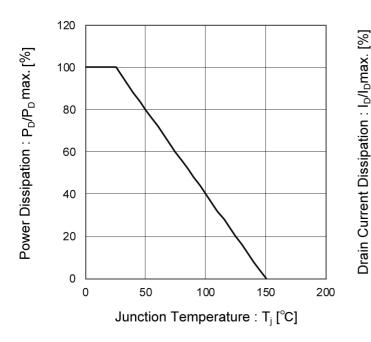


Fig.2 Drain Current Derating Curve

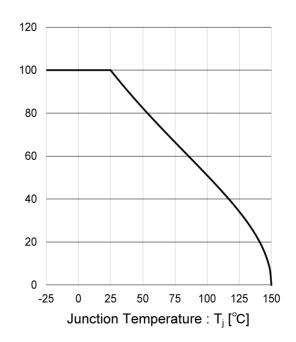


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

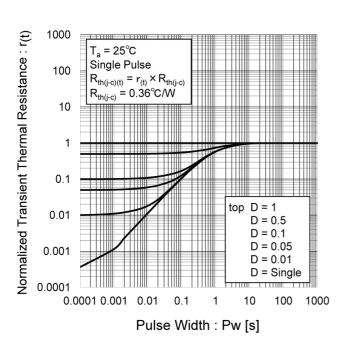
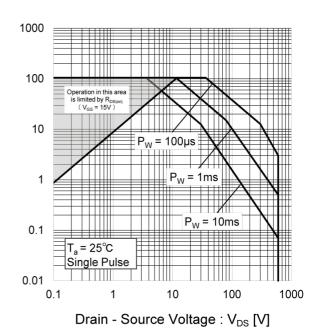


Fig.4 Maximum Safe Operating Area



Drain Current : I<sub>D</sub> [A]

Fig.5 Avalanche Energy Derating Curve

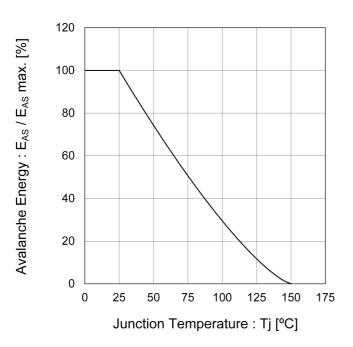


Fig.6 Normalized Breakdown Voltage vs. Junction Temperature

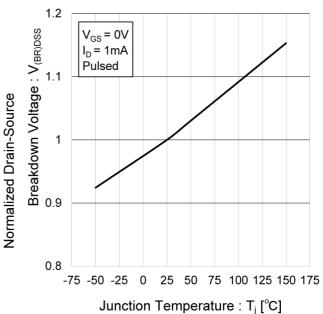


Fig.7 Output Characteristics(I)

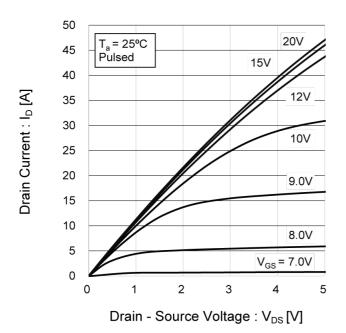
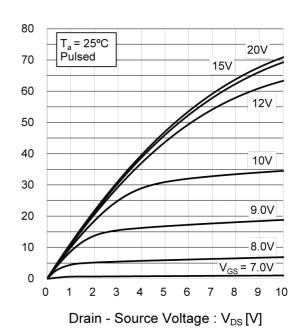


Fig.8 Output Characteristics(II)



Drain Current : I<sub>D</sub> [A]

Fig.9 Gate Threshold Voltage vs. Drain current

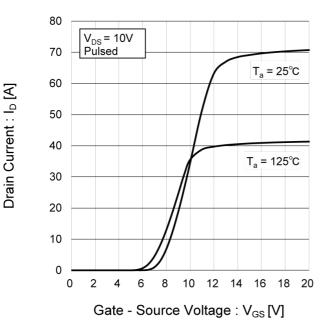


Fig.10 Normalized Gate Threshold .

Voltage vs Junction Temperature

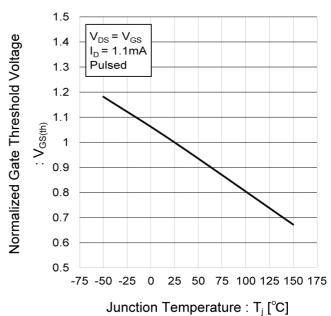


Fig.11 Static Drain - Source On - State Resistance vs. Gate Source Voltage

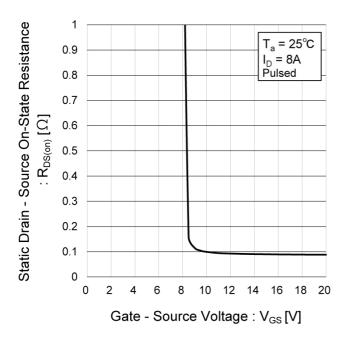


Fig.12 Normalized Static Drain - Source On - State Resistance vs. Junction Temperature

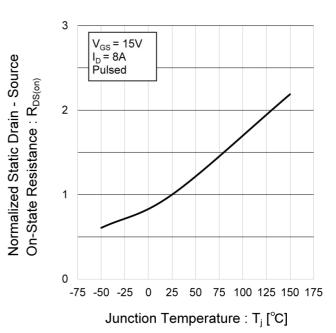


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current

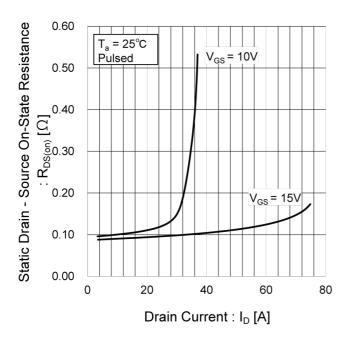


Fig.14 Capacitances

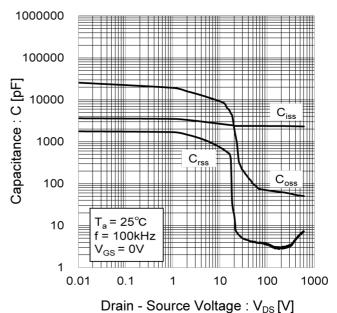


Fig.15 Coss Stored Energy

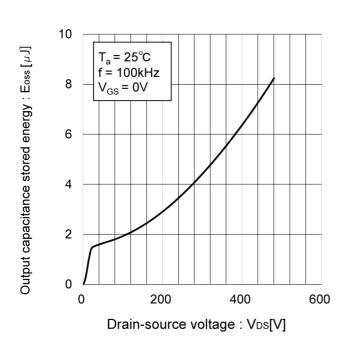
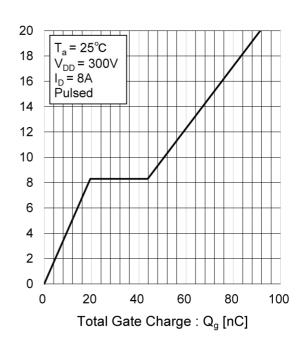
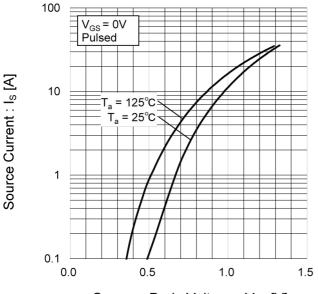


Fig.16 Gate Charge



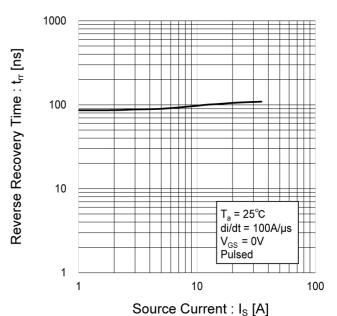
Gate - Source Voltage : V<sub>GS</sub> [V]

Fig.17 Source Current vs. Source - Drain Voltage



Source - Drain Voltage : V<sub>SD</sub> [V]

Fig.18 Reverse Recovery Time vs. Source Current



# Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

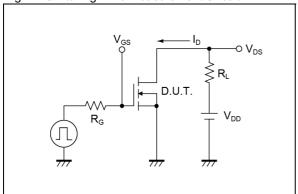


Fig.2-1 Gate Charge Measurement Circuit

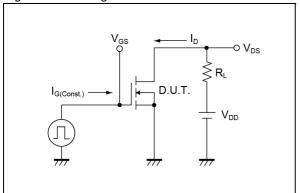


Fig.3-1 Avalanche Measurement Circuit

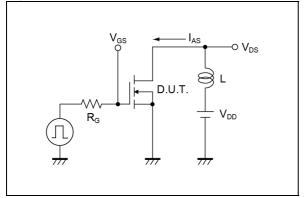


Fig.4-1 trr Measurement Circuit

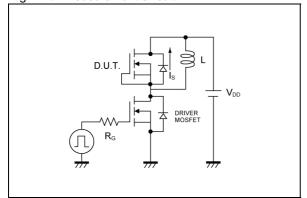


Fig.1-2 Switching Waveforms

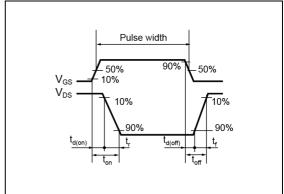


Fig.2-2 Gate Charge Waveform

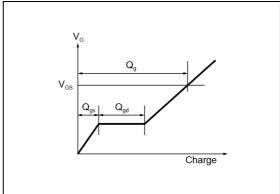


Fig.3-2 Avalanche Waveform

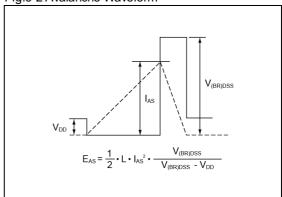
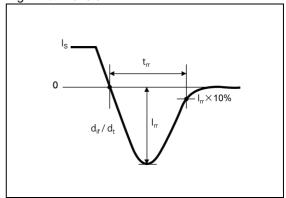
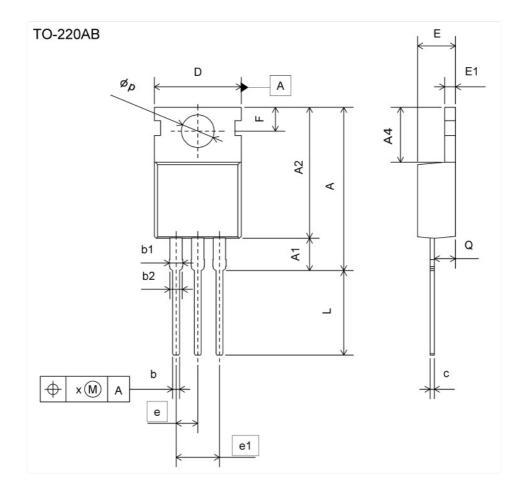


Fig.4-2 trr Waveform



# Dimensions



| DIM      | MILIME | ETERS | INC      | HES   |
|----------|--------|-------|----------|-------|
| DIM      | MIN    |       | MIN      | MAX   |
| Α        | 18.30  | 20.00 | 0.720    | 0.787 |
| A1       | 3.60   | 4.00  | 0.142    | 0.157 |
| A2       | 14.70  | 16.00 | 0.579    | 0.630 |
| A4       | 6.30   | 6.60  | 0.248    | 0.260 |
| b        | 0.65   | 0.95  | 0.026    | 0.037 |
| b1       | 1.20   | 1.75  | 0.047    | 0.069 |
| b2       | 1.20   | 1.70  | 0.047    | 0.067 |
| С        | 0.35   | 0.65  | 0.014    | 0.026 |
| D        | 9.96   | 10.36 | 0.392    | 0.408 |
| E        | 4.24   | 4.64  | 0.167    | 0.183 |
| E1       | 1.14   | 1.40  | 0.045    | 0.055 |
| е        | 2.     | 54    | 0.1      | 100   |
| e1       | 5.     | 08    | 0.2      | 200   |
| F        | 2.60   | 3.00  | 0.102    | 0.118 |
| L        | 9.47   | 10.37 | 0.373    | 0.408 |
| $\phi$ p | 3.69   | 3.99  | 0.145    | 0.157 |
| Q        | 2.30   | 2.70  | 0.091    | 0.106 |
| х        | -0     | 0.38  | <u>=</u> | 0.015 |

Dimension in mm/inches



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| JÁPAN    | USA      | EU         | CHINA   |
|----------|----------|------------|---------|
| CLASSIII | 00/1     | CLASS II b | OTHITI  |
|          | CLASSII  |            | CLASSⅢ  |
| CLASSIV  | 02,10011 | CLASSⅢ     | 02,1002 |

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  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
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- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

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- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

## **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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